

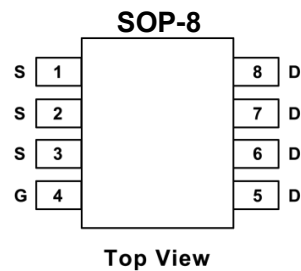
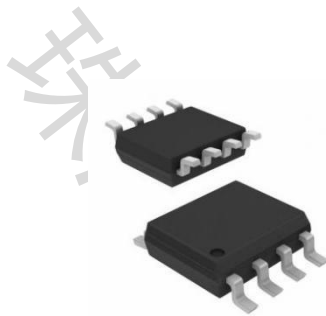
## IRF7341TRPBF-HX P-Channel 60-V (D-S) MOSFET

## PRODUCT SUMMARY

| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω)           | I <sub>D</sub> (A) |
|---------------------|-----------------------------------|--------------------|
| 60                  | 0.040 at V <sub>GS</sub> = - 10 V | 7                  |
|                     | 0.055 at V <sub>GS</sub> = 4.5 V  |                    |

## FEATURES

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested

Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

| Parameter                                      |                      | Symbol                            | Maximum    | Units |
|--|----------------------|-----------------------------------|------------|-------|
| Drain-Source Voltage                           |                      | V <sub>DS</sub>                   | 60         | V     |
| Gate-Source Voltage                            |                      | V <sub>GS</sub>                   | ±20        | V     |
| Continuous Drain Current <sup>AF</sup>         | T <sub>A</sub> =25°C | I <sub>D</sub>                    | 4.5        | A     |
|  | T <sub>A</sub> =70°C |                                   | 3.6        |       |
| Pulsed Drain Current <sup>B</sup>              |                      | I <sub>DM</sub>                   | 20         |       |
| Power Dissipation                              | T <sub>A</sub> =25°C | P <sub>D</sub>                    | 2          | W     |
|  | T <sub>A</sub> =70°C |                                   | 1.28       |       |
| Avalanche Current <sup>B</sup>                 |                      | I <sub>AR</sub> , I <sub>AS</sub> | 19         | A     |
| Repetitive avalanche energy 0.1mH <sup>B</sup> |                      | E <sub>AR</sub> , E <sub>AS</sub> | 18         | mJ    |
| Junction and Storage Temperature Range         |                      | T <sub>J</sub> , T <sub>STG</sub> | -55 to 150 | °C    |

## Thermal Characteristics

| Parameter                                |              | Symbol           | Typ | Max  | Units |
|--|--------------|------------------|-----|------|-------|
| Maximum Junction-to-Ambient <sup>A</sup> | t ≤ 10s      | R <sub>θJA</sub> | 48  | 62.5 | °C/W  |
| Maximum Junction-to-Ambient <sup>A</sup> | Steady-State |                  | 74  | 110  | °C/W  |
| Maximum Junction-to-Lead <sup>C</sup>    | Steady-State | R <sub>θJL</sub> | 35  | 60   | °C/W  |

| Electrical Characteristics (T <sub>J</sub> =25° C, unless otherwise noted) |  |  |     |          |           |       |
|--|--|--|-----|----------|-----------|-------|
| Symbol   | Parameter                              | Conditions   | Min | Typ      | Max       | Units |
| <b>STATIC PARAMETERS</b>   |  |  |     |          |           |       |
| BV <sub>DSS</sub>  | Drain-Source Breakdown Voltage         | I <sub>D</sub> =250μA, V <sub>GS</sub> =0V   | 60  |          |           | V     |
| I <sub>DSS</sub>   | Zero Gate Voltage Drain Current        | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V<br>T <sub>J</sub> =55°C                                  |     |          | 1<br>5    | μA    |
| I <sub>GSS</sub>   | Gate-Body leakage current              | V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V   |     |          | 100       | nA    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage                 | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA   | 1   | 2.1      | 3         | V     |
| I <sub>D(ON)</sub>   | On state drain current                 | V <sub>GS</sub> =10V, V <sub>DS</sub> =5V  | 20  |          |           | A     |
| R <sub>DS(ON)</sub>  | Static Drain-Source On-Resistance      | V <sub>GS</sub> =10V, I <sub>D</sub> =4.5A<br>T <sub>J</sub> =125°C                                |     | 46<br>80 | 56<br>100 | mΩ    |
|  |  | V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A  |     | 64       | 77        | mΩ    |
|  |  |  |     |          |           |       |
| g <sub>FS</sub>  | Forward Transconductance               | V <sub>DS</sub> =5V, I <sub>D</sub> =4.5A  |     | 11       |           | S     |
| V <sub>SD</sub>  | Diode Forward Voltage                  | I <sub>S</sub> =1A, V <sub>GS</sub> =0V  |     | 0.74     | 1         | V     |
| I <sub>S</sub>   | Maximum Body-Diode Continuous Current  |  |     |          | 3         | A     |
| I <sub>SM</sub>  | Pulsed Body Diode Current <sup>B</sup> |  |     |          | 20        | A     |
| <b>DYNAMIC PARAMETERS</b>  |  |  |     |          |           |       |
| C <sub>iss</sub>   | Input Capacitance                      | V <sub>GS</sub> =0V,   |     | 450      | 540       | pF    |
| C <sub>oss</sub>   | Output Capacitance                     | V <sub>DS</sub> =30V,  |     | 60       |           | pF    |
| C <sub>rss</sub>   | Reverse Transfer Capacitance           | f=1MHz   |     | 25       |           | pF    |
| R <sub>g</sub>   | Gate resistance                        | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz   | 1.3 | 1.65     | 2         | Ω     |
| <b>SWITCHING PARAMETERS</b>  |  |  |     |          |           |       |
| Q <sub>g</sub> (10V)   | Total Gate Charge                      | V <sub>GS</sub> =10V,<br>V <sub>DS</sub> =30V,   |     | 8.5      | 10.5      | nC    |
| Q <sub>g</sub> (4.5V)  | Total Gate Charge                      |  |     | 4.3      | 5.5       | nC    |
| Q <sub>gs</sub>  | Gate Source Charge                     |  |     | 1.6      |           | nC    |
| Q <sub>gd</sub>  | Gate Drain Charge                      |  |     | 2.2      |           | nC    |
| t <sub>D(on)</sub>   | Turn-On DelayTime                      | V <sub>GS</sub> =10V,<br>V <sub>DS</sub> =30V,<br>R <sub>L</sub> =6.7Ω,<br>R <sub>DS(on)</sub> =3Ω |     | 4.7      |           | ns    |
| t <sub>r</sub>   | Turn-On Rise Time                      |  |     | 2.3      |           | ns    |
| t <sub>D(off)</sub>  | Turn-Off DelayTime                     |  |     | 15.7     |           | ns    |
| t <sub>f</sub>   | Turn-Off Fall Time                     |  |     | 1.9      |           | ns    |
| t <sub>rr</sub>  | Body Diode Reverse Recovery Time       | I <sub>F</sub> =4.5A, dI/dt=100A/μs  |     | 27.5     | 35        | ns    |
| Q <sub>rr</sub>  | Body Diode Reverse Recovery Charge     | I <sub>F</sub> =4.5A, dI/dt=100A/μs  |     | 32       |           | nC    |

**NOTE**

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design.

B. Repetitive rating, pulse width limited by junction temperature.

C. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

F. The current rating is based on the t<sub>s</sub> 10s junction to ambient thermal resistance rating.

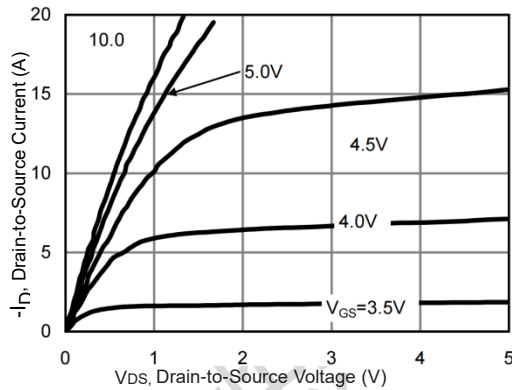


Fig 1. Typical Output Characteristics

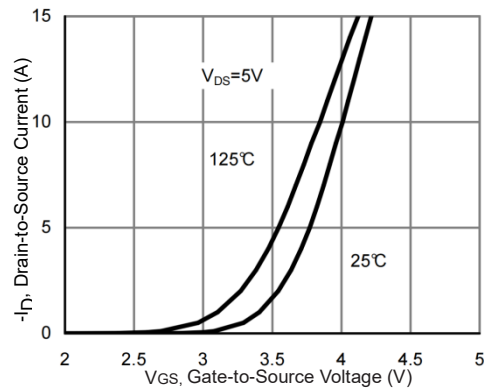


Fig 2. Typical Transfer Characteristics

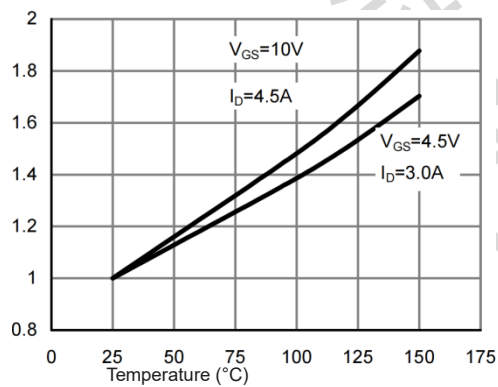


Fig 3. On-Resistance vs. Junction Temperature

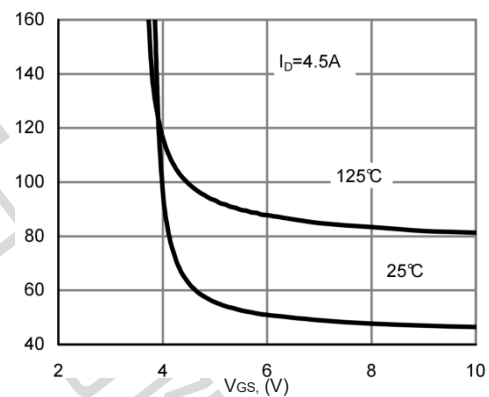
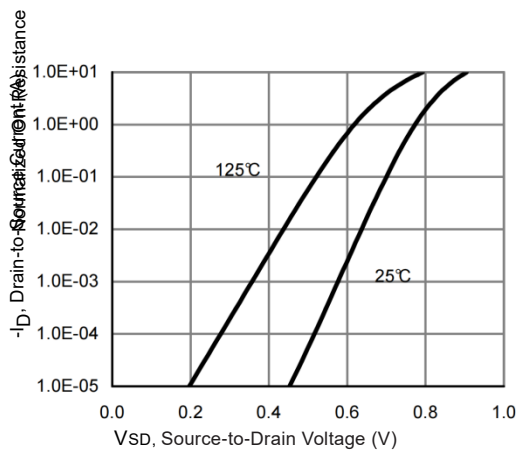
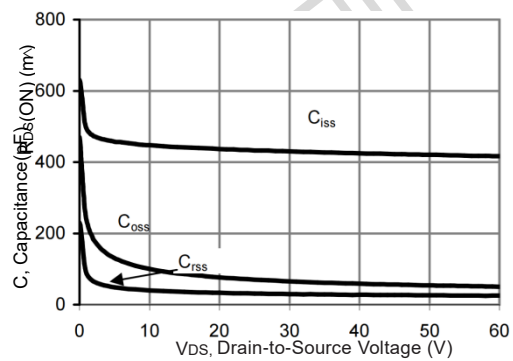


Fig 4. On-Resistance vs. Gate-Source Voltage

Fig 5. Typical Source-Drain Diode  
Forward VoltageFig 6. Typical Capacitance Vs.  
Drain-to-Source Voltage

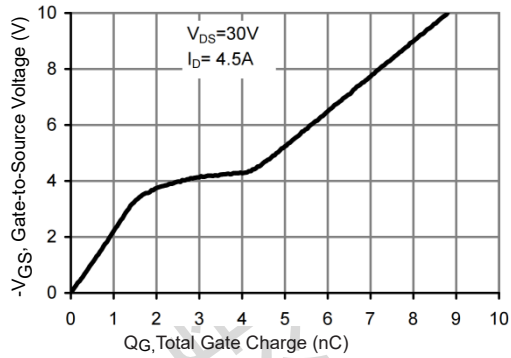


Fig 7. Gate Charge Characteristics

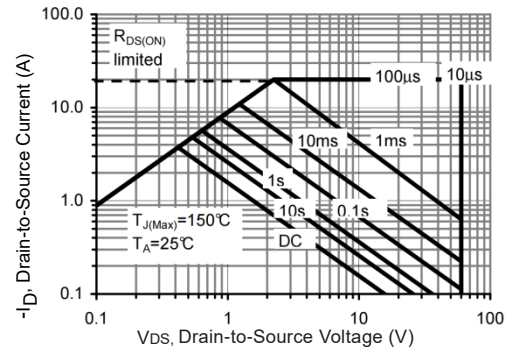


Fig 8. Maximum Safe Operating Area (Note E)

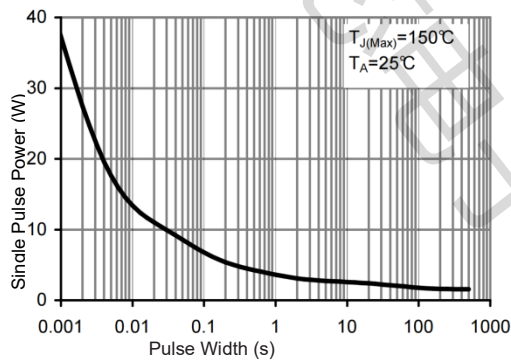
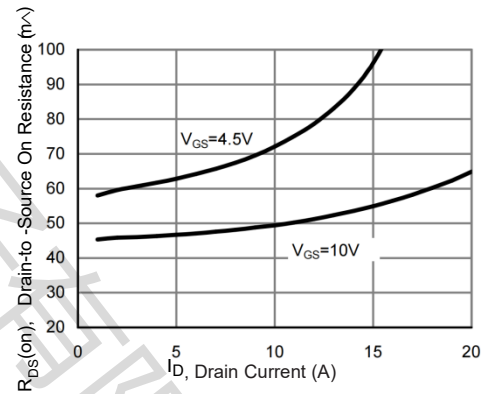
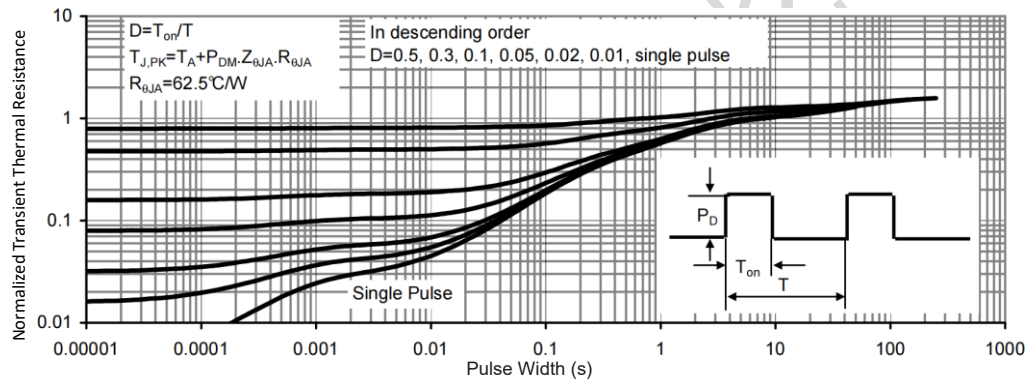
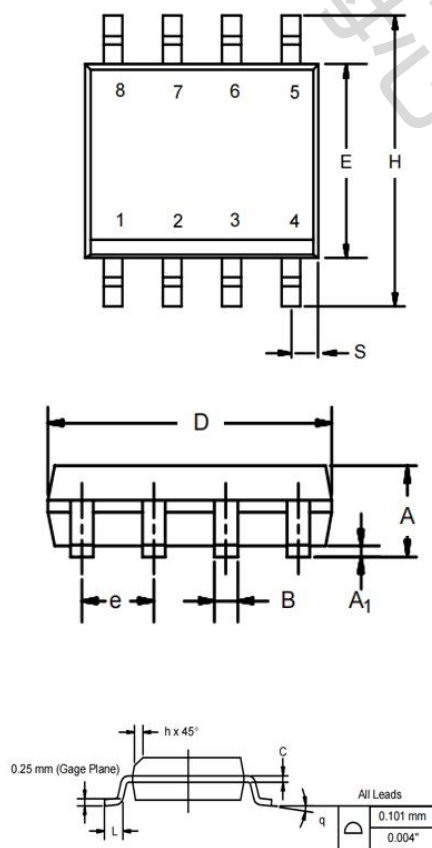
Fig 9. Single Pulse Power Rating  
Junction-to-Ambient (Note E)Fig 10. On-Resistance vs. Drain  
Current and Gate Voltage

Fig 11. Normalized Maximum Transient Thermal Impedance

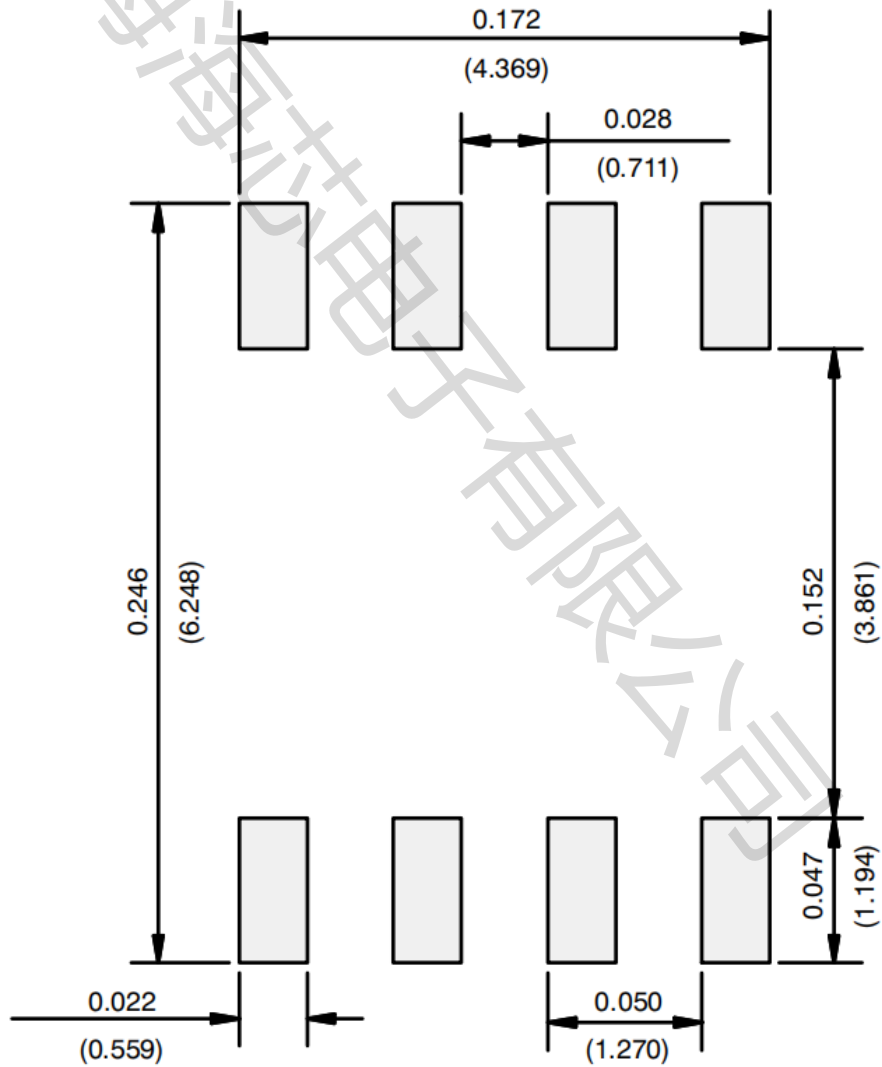
## SOP-8 Package Outline

Dimensions are shown in millimeters (inches)



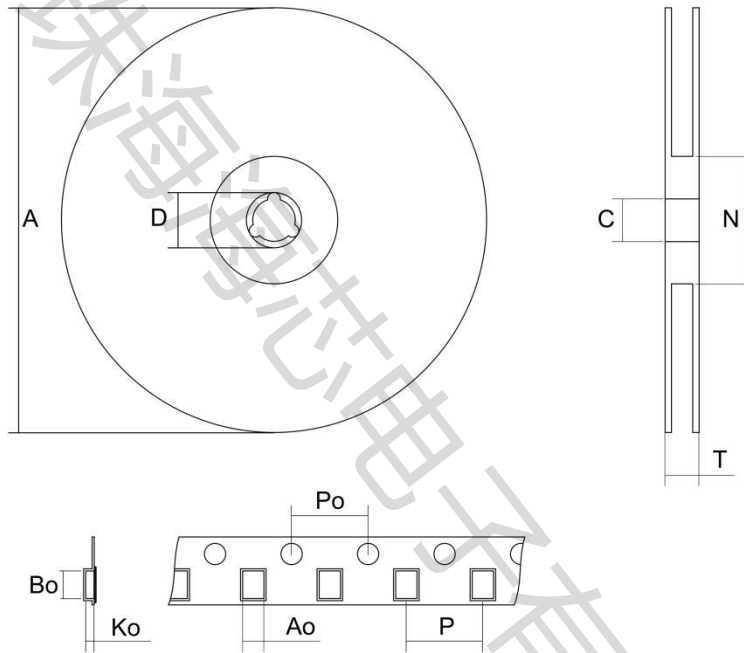
| DIM | MILLIMETERS |      | INCHES     |       |
|-----|-------------|------|------------|-------|
|     | Min         | Max  | Min        | Max   |
| A   | 1.35        | 1.75 | 0.053      | 0.069 |
| A1  | 0.10        | 0.20 | 0.004      | 0.008 |
| B   | 0.35        | 0.51 | 0.014      | 0.020 |
| C   | 0.19        | 0.25 | 0.007<br>5 | 0.010 |
| D   | 4.80        | 5.00 | 0.189      | 0.196 |
| E   | 3.80        | 4.00 | 0.150      | 0.157 |
| e   | 1.27 BSC    |      | 0.050 BSC  |       |
| H   | 5.80        | 6.20 | 0.228      | 0.244 |
| h   | 0.25        | 0.50 | 0.010      | 0.020 |
| L   | 0.50        | 0.93 | 0.020      | 0.037 |
| q   | 0°          | 8°   | 0°         | 8°    |
| S   | 0.44        | 0.64 | 0.018      | 0.026 |

**RECOMMENDED MINIMUM PADS FOR SOP-8**

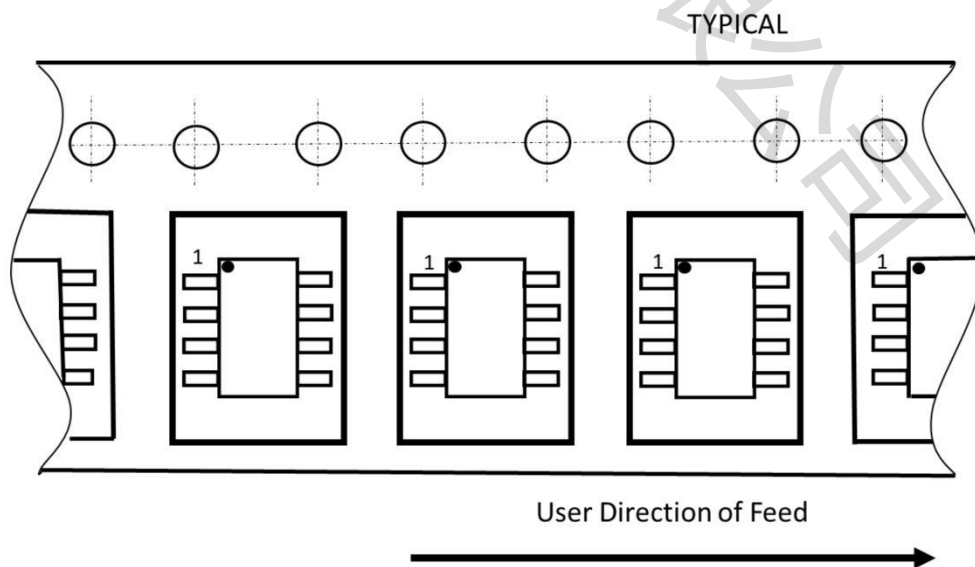


## SOP-8 packing information

### SOP-8 tape and reel



### Tape orientation



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